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PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10073506	FILING DATE 02/11/2002	CLASS 428-	SUBCLASS 4146	GAU 1775-	EXAMINER S. H. T.
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\*\*APPLICANT'S: Falster Robert; Binns Martin; Wang Alan;

\*\*CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/416,998 10/13/1999

WHICH CLAIMS BENEFIT OF 60/104,304 10/14/1998

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\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met		<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO MEMC 98-1451/2554.1
Verified and Acknowledged Examiners's initials			
TITLE : Thermal annealing process for producing low defect density single crystal silicon U.S. DEPT. OF COMM./PAT. & TM. PT 2-436L (Rev. 12-94)			

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED		
			Total Claims	Print Claim for O.G.	
ISSUE FEE		DRAWING			
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.	Print Fig.	
TERMINAL DISCLAIMER		Application Examiner			
PREPARED FOR ISSUE					
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